

Silicon Carbide Power Schottky Diode

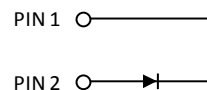
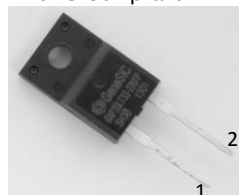
V_{RRM}	=	3300 V
I_F ($T_C \leq 125^\circ\text{C}$)	=	0.3 A
Q_C	=	20 nC

Features

- Industry's leading low leakage currents
- 175 °C maximum operating temperature
- Electrically isolated base-plate
- Positive temperature coefficient of V_F
- Fast switching speeds
- Superior figure of merit Q_C/I_F

Package

- RoHS Compliant



TO – 220FP (Isolated Base-plate Package)

Advantages

- Low standby power losses
- Improved circuit efficiency (Lower overall cost)
- Significantly reduced switching losses compare to Si PIN diodes
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance

Applications

- Down Hole Oil Drilling, Geothermal Instrumentation
- High Voltage Multipliers
- Military Power Supplies

Maximum Ratings at $T_j = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		3300	V
Continuous forward current	I_F	$T_C \leq 125^\circ\text{C}$	0.3	A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 125^\circ\text{C}$	0.35	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms	2	A
		$T_C = 125^\circ\text{C}$, $t_p = 10$ ms	1	A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, $t_p = 10$ μs	10	A
I^2t value	$\int I^2 dt$	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms	0.1	A^2S
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$	89	W
Operating and storage temperature	T_j, T_{stg}		-55 to 175	$^\circ\text{C}$

Electrical Characteristics at $T_j = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 0.3$ A, $T_j = 25^\circ\text{C}$ $I_F = 0.3$ A, $T_j = 175^\circ\text{C}$		1.7 4.0	2.2 5.0	V
Reverse current	I_R	$V_R = 3300$ V, $T_j = 25^\circ\text{C}$ $V_R = 3300$ V, $T_j = 175^\circ\text{C}$		1 10	10 100	μA
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ $dI_F/dt = 35$ A/ μs $T_j = 175^\circ\text{C}$		20		nC
Switching time	t_s	$V_R = 1500$ V		< 60		ns
Total capacitance	C	$V_R = 1$ V, $f = 1$ MHz, $T_j = 25^\circ\text{C}$		42		pF
		$V_R = 400$ V, $f = 1$ MHz, $T_j = 25^\circ\text{C}$		8		
		$V_R = 1000$ V, $f = 1$ MHz, $T_j = 25^\circ\text{C}$		7		

Thermal Characteristics

Thermal resistance, junction – Cu lead frame	R_{thJC}	1.69	$^\circ\text{C/W}$
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Mechanical Properties

Mounting torque, M3 screw	M	0.6	Nm
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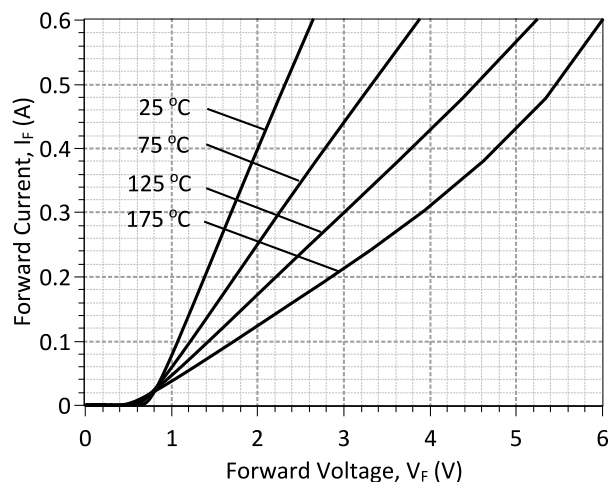


Figure 1: Typical Forward Characteristics

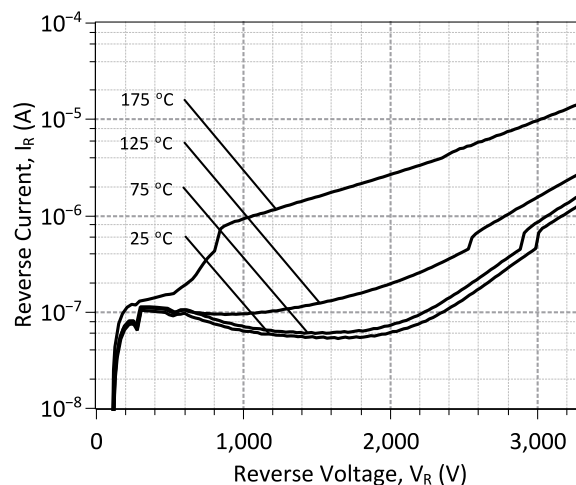


Figure 2: Typical Reverse Characteristics

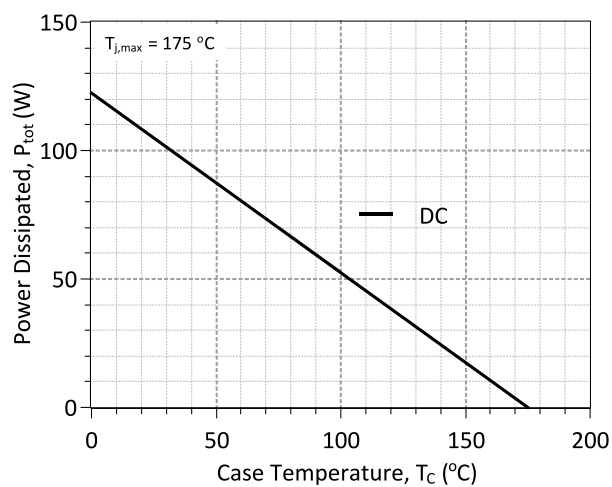
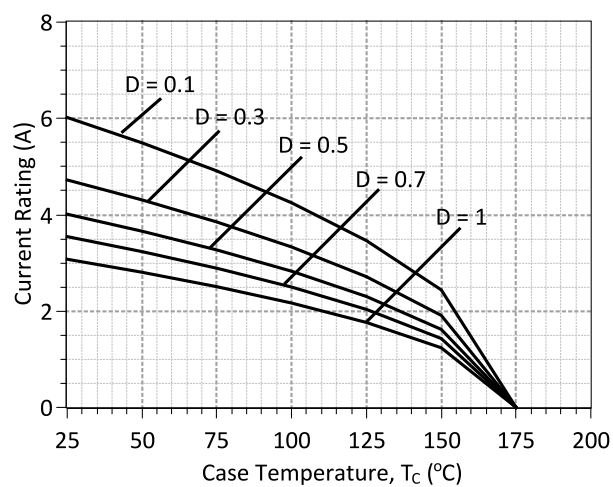


Figure 3: Power Derating Curve



**Figure 4: Current Derating Curves ($D = t_p/T$, $t_p = 400 \mu s$)
(Considering worst case Zth conditions)**

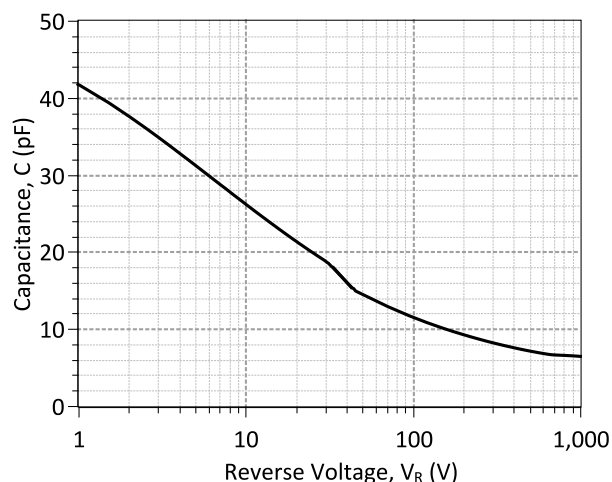


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

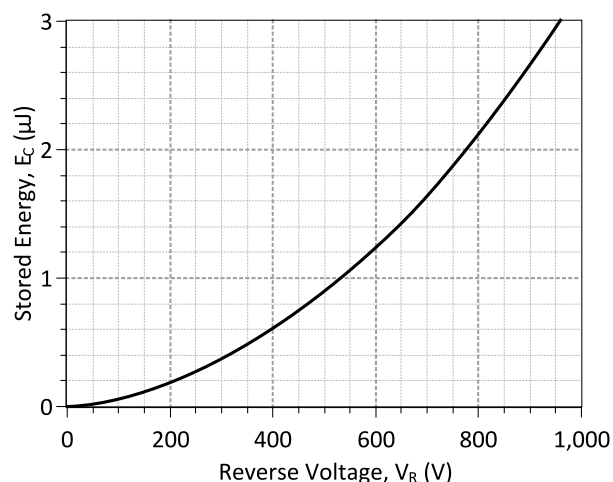
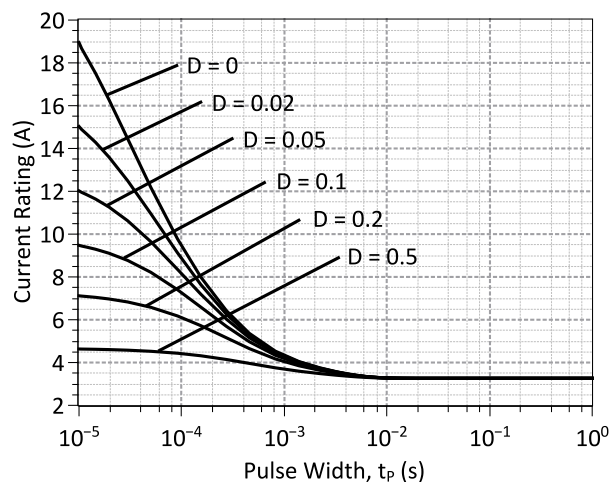
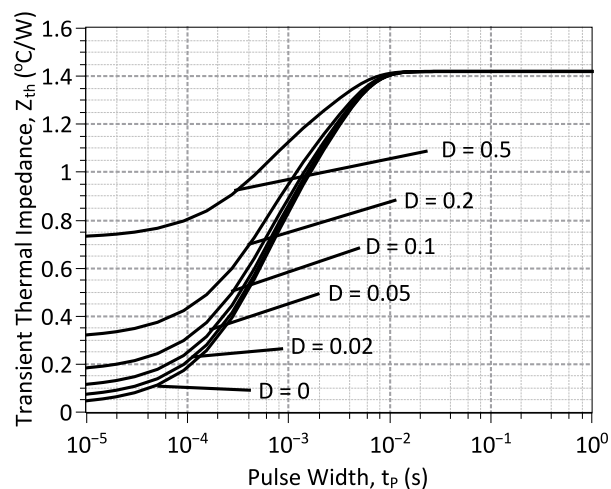
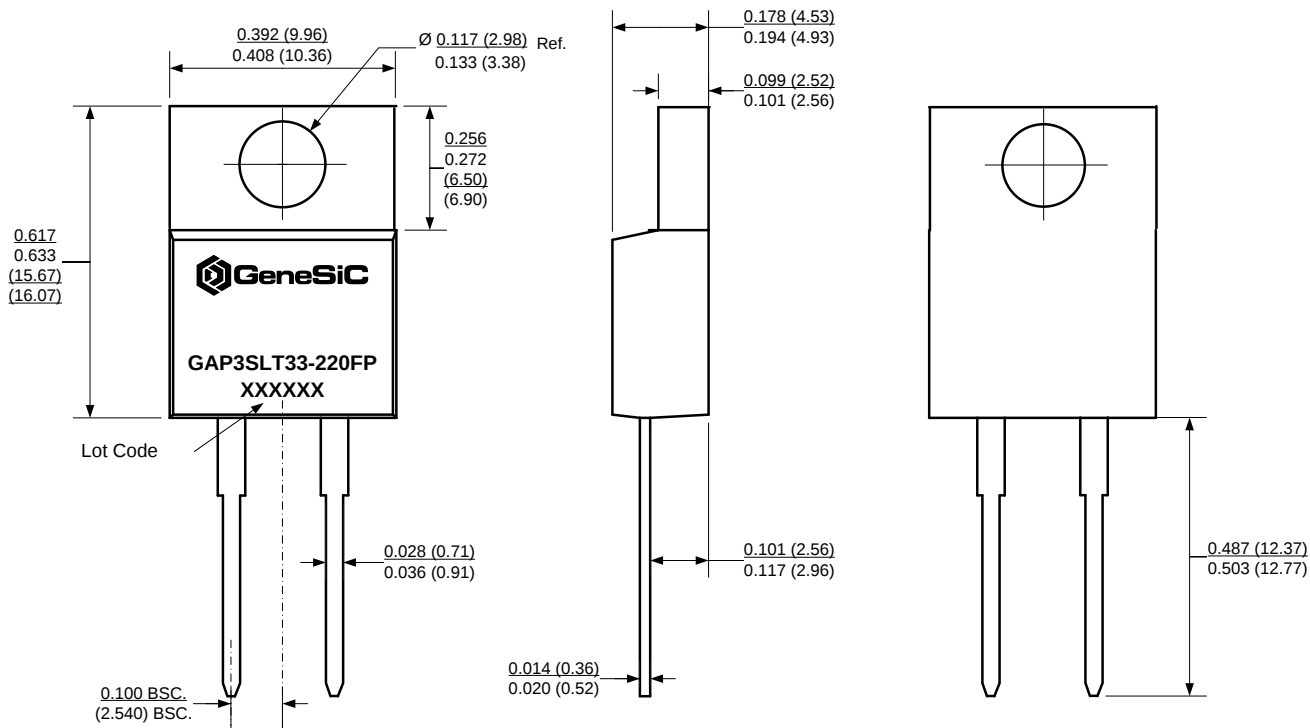


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics


Figure 7: Current vs Pulse Duration Curves at $T_c = 150\text{ }^{\circ}\text{C}$

Figure 8: Transient Thermal Impedance
Package Dimensions:
TO-220FP
PACKAGE OUTLINE

NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS
3. CONTROLLED LEAD COPLANARITY <D> 0.004 INCH MAXIMUM

Revision History			
Date	Revision	Comments	Supersedes
2014/12/19	3	Updated Electrical Characteristics	
2014/08/26	2	Updated Electrical Characteristics	
2013/03/22	1	Added Thermal Characteristics	
2013/01/23	0	Initial Release	

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SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/products_sic/rectifiers/GAP3SLT33-220FP_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GAP3SLT33-220FP.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      04-SEP-2013    $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GAP3SLT33-220FP SPICE Model
*
.SUBCKT GAP3SLT33 ANODE KATHODE
R1 ANODE INT R=((TEMP-24)*0.0535); Temperature Dependant Resistor
D1 INT KATHODE GAP3SLT33_25C; Call the 25C Diode Model
D2 ANODE KATHODE GAP3SLT33_PIN; Call the PiN Diode Model
.MODEL GAP3SLT33_25C D
+ IS      1.39E-14      RS      2.88
+ N       1.0120127     IKF     36.05007504
+ EG      1.2           XTI     -3
+ CJO     6.01E-11      VJ      0.924257443
+ M       0.3084545     FC      0.5
+ TT      1.00E-10      BV      3300
+ IBV     1.00E-03      VPK     3300
+ IAVE     3.00E-01     TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
.MODEL GAP3SLT33_PIN D
+ IS      178.99E-18    RS      15
+ N       5             EG      3.23
+ XTI     50           FC      0.5
+ TT      0            BV      3300
+ IBV     1.00E-03      VPK     3300
+ IAVE     3.00E-01     TYPE    SiC_PiN
.ENDS
* End of GAP3SLT33-220FP SPICE Model
```

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<http://moschip.ru/get-element>

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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